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(54) **SOLID-STATE IMAGING APPARATUS AND ELECTRONIC APPARATUS**

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(57) **ABSTRACT**

A solid-state imaging apparatus includes a pixel array in which a plurality of pixels are two-dimensionally arranged, wherein each pixel has a first photoelectric conversion region formed above a semiconductor layer, a second photoelectric conversion region formed in the semiconductor layer, a first filter configured to transmit a light in a predetermined wavelength region corresponding to a color component, and a second filter having different transmission characteristics from the first filter. One photoelectric conversion region out of the first photoelectric conversion region and the second photoelectric conversion region photoelectrically converts light in a visible light region, the other photoelectric conversion region photoelectrically converts light in an infrared region, the first filter is formed above the first photoelectric conversion region, and the second filter has transmission characteristics of making wavelengths of lights in an infrared region absorbed in the other photoelectric conversion region formed below the first filter the same.